



P-Channel Silicon MOSFET

# ATP112 — General-Purpose Switching Device Applications

## Features

- ON-resistance  $R_{DS(on)1}=33m\Omega$ (typ.)
- 4V drive
- Protection diode in
- Input Capacitance  $C_{iss}=1450pF$ (typ.)
- Halogen free compliance

## Specifications

Absolute Maximum Ratings at  $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		-60	V
Gate-to-Source Voltage	$V_{GSS}$		$\pm 20$	V
Drain Current (DC)	$I_D$		-25	A
Drain Current ( $PW \leq 10\mu s$ )	$I_{DP}$	$PW \leq 10\mu s$ , duty cycle $\leq 1\%$	-75	A
Allowable Power Dissipation	$P_D$	$T_c=25^\circ C$	40	W
Channel Temperature	$T_{ch}$		150	$^\circ C$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ C$
Avalanche Energy (Single Pulse) *1	$E_{AS}$		50	mJ
Avalanche Current *2	$I_{AV}$		-13	A

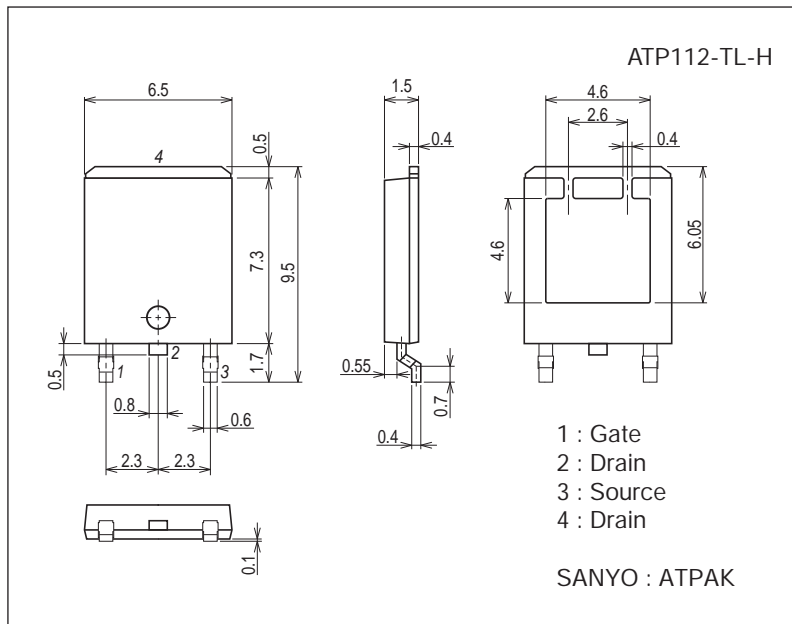
Note : \*1  $V_{DD}=-10V$ ,  $L=500\mu H$ ,  $I_{AV}=-13A$

\*2  $L \leq 500\mu H$ , Single pulse

## Package Dimensions

unit : mm (typ)

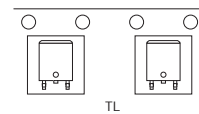
7057-001



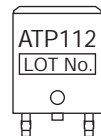
## Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

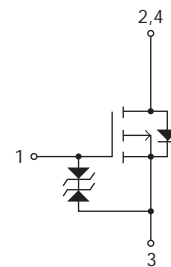
## Packing Type: TL



## Marking



## Electrical Connection

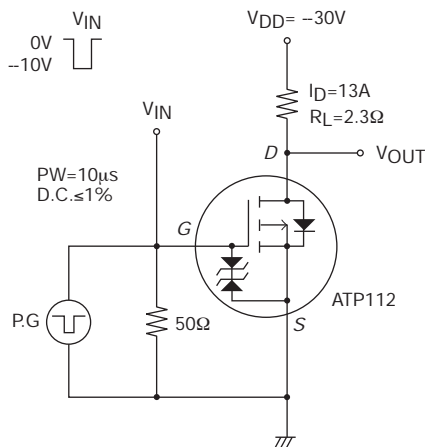


# ATP112

## Electrical Characteristics at Ta=25°C

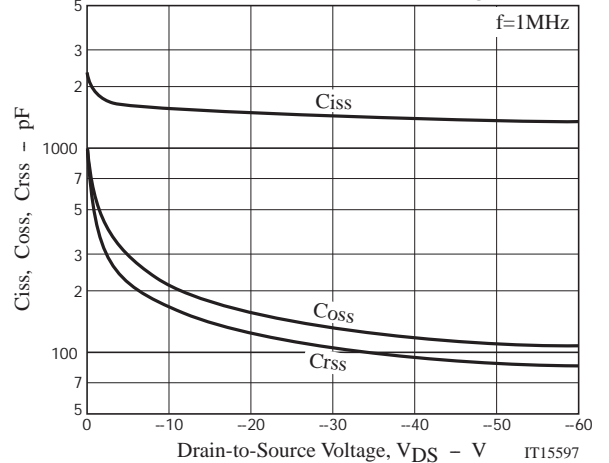
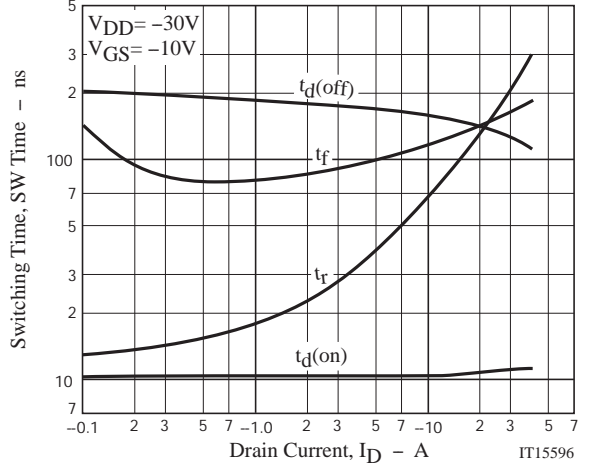
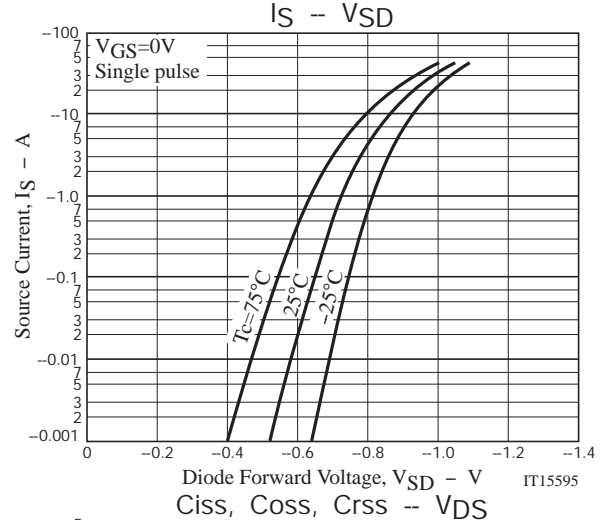
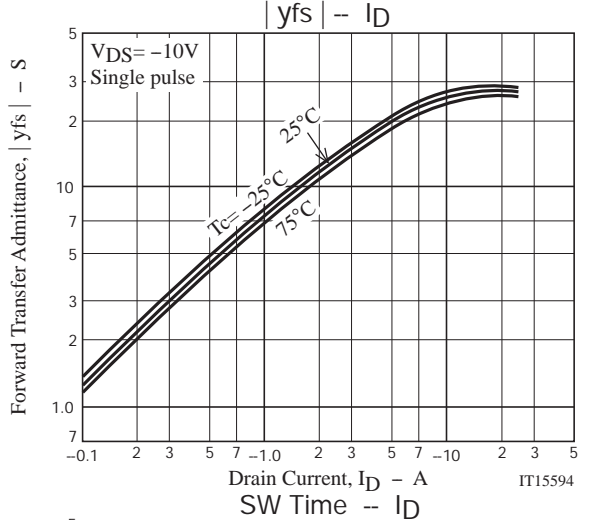
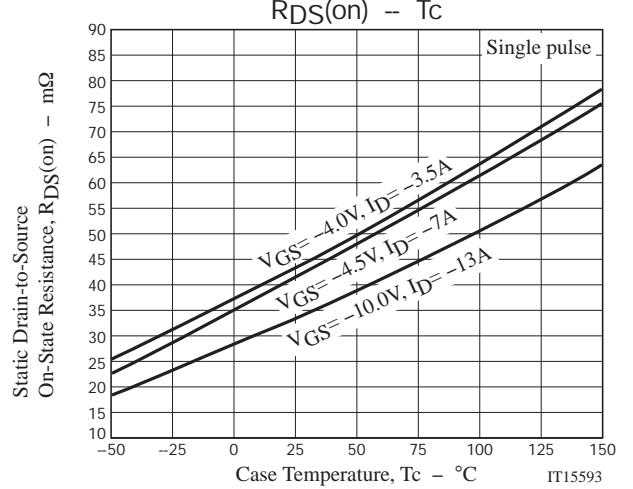
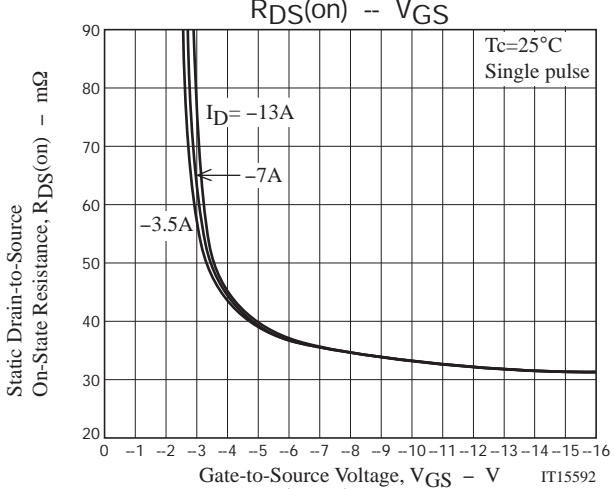
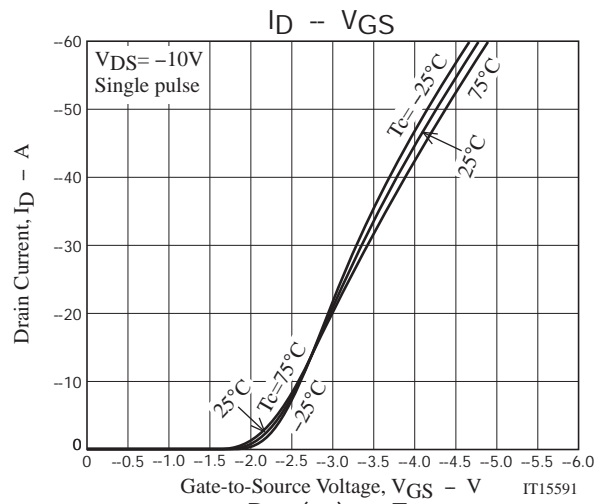
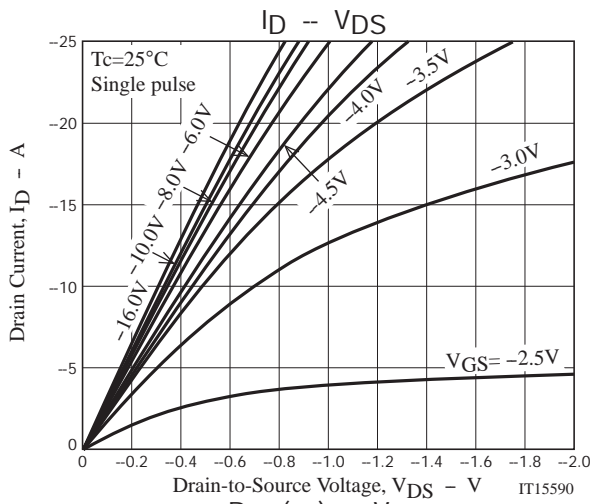
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}, V_{GS} = 0\text{V}$	-60			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -60\text{V}, V_{GS} = 0\text{V}$			-1	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$			$\pm 10$	$\mu\text{A}$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}, I_D = -1\text{mA}$	-1.2		-2.6	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = -10\text{V}, I_D = -13\text{A}$		24		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)1}$	$I_D = -13\text{A}, V_{GS} = -10\text{V}$		33	43	$\text{m}\Omega$
	$R_{DS(on)2}$	$I_D = -7\text{A}, V_{GS} = -4.5\text{V}$		42	59	$\text{m}\Omega$
	$R_{DS(on)3}$	$I_D = -3.5\text{A}, V_{GS} = -4\text{V}$		45	63	$\text{m}\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -20\text{V}, f = 1\text{MHz}$		1450		pF
Output Capacitance	$C_{oss}$			155		pF
Reverse Transfer Capacitance	$C_{rss}$			125		pF
Turn-ON Delay Time	$t_d(on)$			10		ns
Rise Time	$t_r$	See specified Test Circuit.		80		ns
Turn-OFF Delay Time	$t_d(off)$			150		ns
Fall Time	$t_f$			120		ns
Total Gate Charge	$Q_g$	$V_{DS} = -30\text{V}, V_{GS} = -10\text{V}, I_D = -25\text{A}$		33.5		nC
Gate-to-Source Charge	$Q_{gs}$			5.3		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$			7.9		nC
Diode Forward Voltage	$V_{SD}$		$I_S = -25\text{A}, V_{GS} = 0\text{V}$		-0.97	-1.5

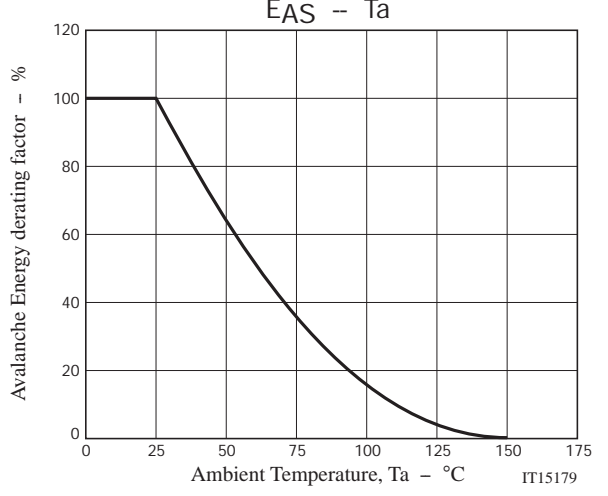
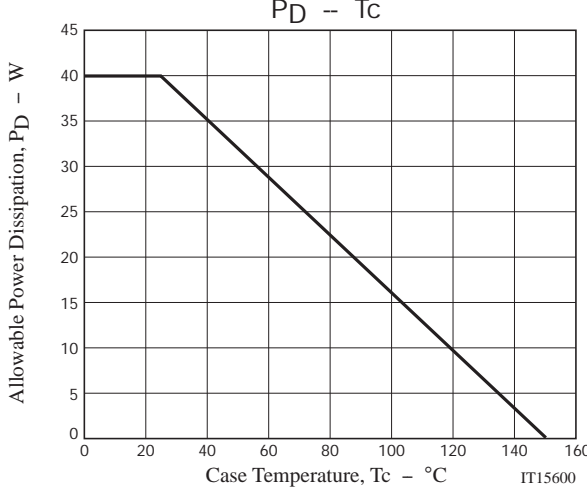
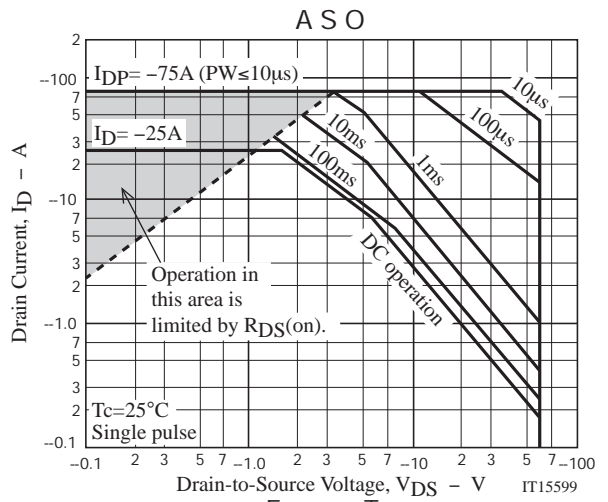
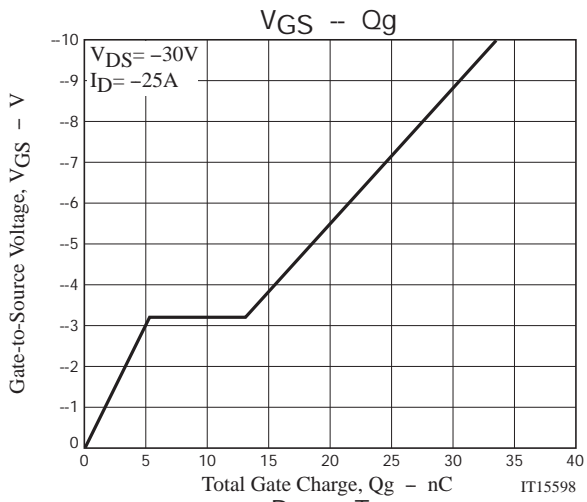
## Switching Time Test Circuit



## Ordering Information

Device	Package	Shipping	memo
ATP112-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free





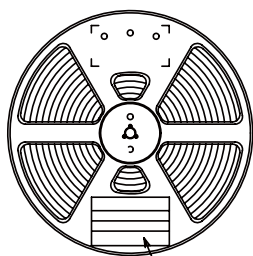
Taping Specification

ATP112-TL-H

1. Packing Format (TL)

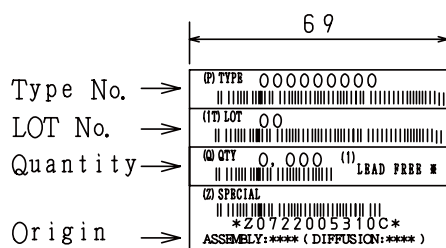
Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

Packing method



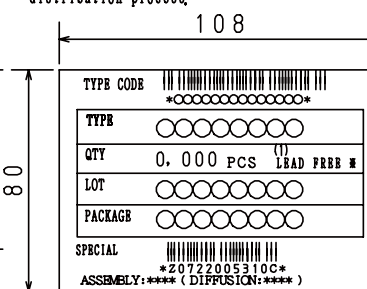
Reel label

Reel label, Inner box label  
(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



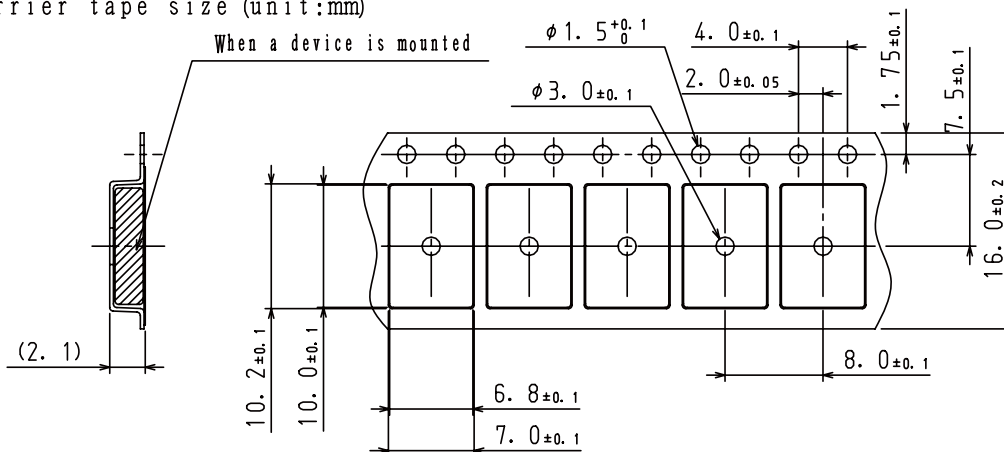
NOTE (1)

The LEAD FREE # description shows that the surface treatment of the terminal is lead free.

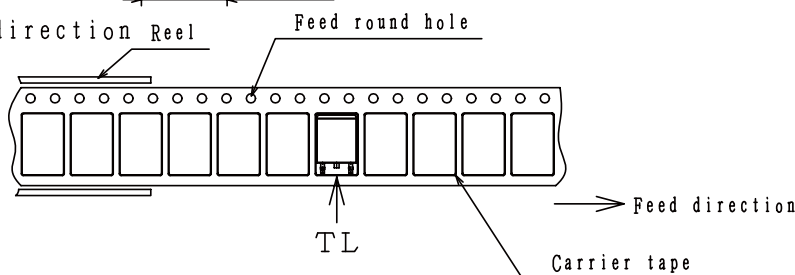
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction Reel



The one electrode terminals on feed hole side...TL

# ATP112

## Outline Drawing

ATP112-TL-H



## Land Pattern Example



Note on usage : Since the ATP112 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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